



DMTH4004SCTB

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> T <sub>C</sub> = +25°C (Note 9)
40V	$3m\Omega @ V_{GS} = 10V$	100A

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

### 40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

### Features

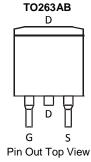
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> Minimizes Power Losses
- Low Q<sub>g</sub> Minimizes Switching Losses
- Lead-Free Finish; RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate
  Datasheet (DMTH4004SCTBQ)

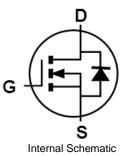
### **Mechanical Data**

- Case: TO263AB
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 3
- Weight: 1.4 grams (Approximate)



Top View





# Ordering Information (Note 4)

Packaging
800 / Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



T4004SCTB = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 14 = 2014) WW = Week (01 to 53)



# **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	40	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 6)	T <sub>C</sub> = +25°C (Note 9)	ID	100	А
	$T_{\rm C} = +100^{\circ}{\rm C}$		100	
Maximum Continuous Body Diode Forward Current		Is	100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	200	A	
Avalanche Current, L=0.2mH	I <sub>AS</sub>	45	А	
Avalanche Energy, L=0.2mH		E <sub>AS</sub>	200	mJ

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	4.7	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ ext{ heta}JA}$	32	°C/W
Total Power Dissipation (Note 6)	T <sub>C</sub> = +25°C	PD	136	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	1.1	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +175	°C

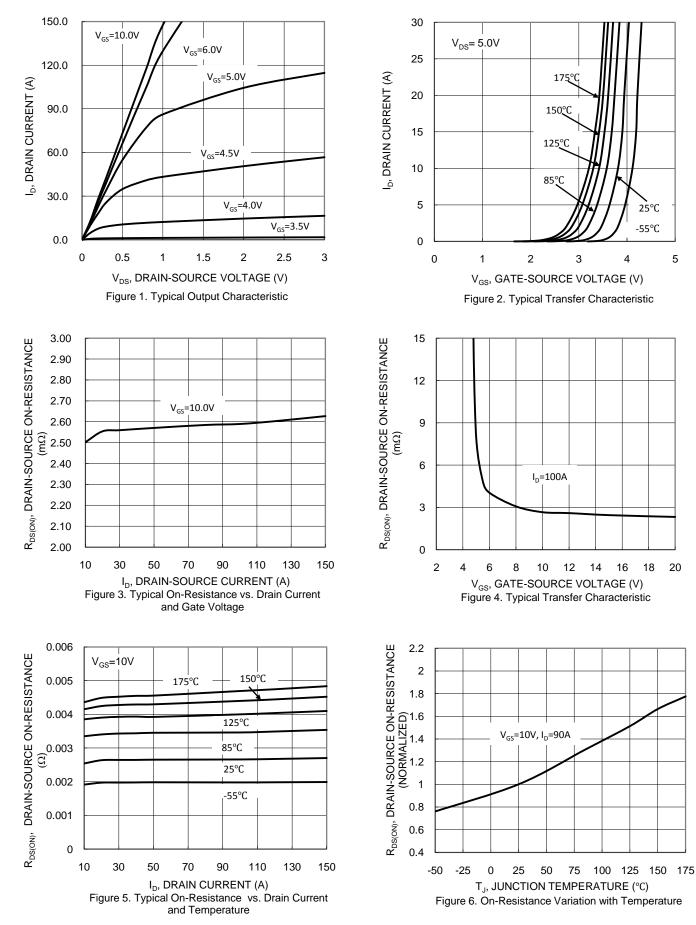
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	_	_	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	—	4	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		2.5	3	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 100A	
Diode Forward Voltage	V <sub>SD</sub>		—	1.3	V	$V_{GS} = 0V, I_{S} = 100A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		4305	—		$V_{DS} = 25V, V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss		1441	—	pF		
Reverse Transfer Capacitance	Crss	_	102	_			
Gate Resistance	R <sub>G</sub>	_	0.77	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg	_	68.6	_		V <sub>DD</sub> = 20V, I <sub>D</sub> = 90A, V <sub>GS</sub> = 10V	
Gate-Source Charge	Q <sub>gs</sub>	_	16.8	_	nC		
Gate-Drain Charge	Q <sub>gd</sub>	_	14.2	—			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	9.5	—			
Turn-On Rise Time	t <sub>R</sub>	_	6.7	_	ns	$V_{DD} = 20V, V_{GS} = 10V,$ $I_D = 90A, R_G = 3.5\Omega$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	26.4	—	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	8.1	_			
Reverse Recovery Time	t <sub>RR</sub>	_	52.4	—	ns		
Reverse Recovery Charge	Q <sub>RR</sub>		78.2	—	nC	I <sub>F</sub> = 50A, di/dt = 100A/μs	

 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 6. Device mounted on infinite heatsink and measured by thermal couple attached on bottom heasink of package.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.
 9. Package limited. Notes:



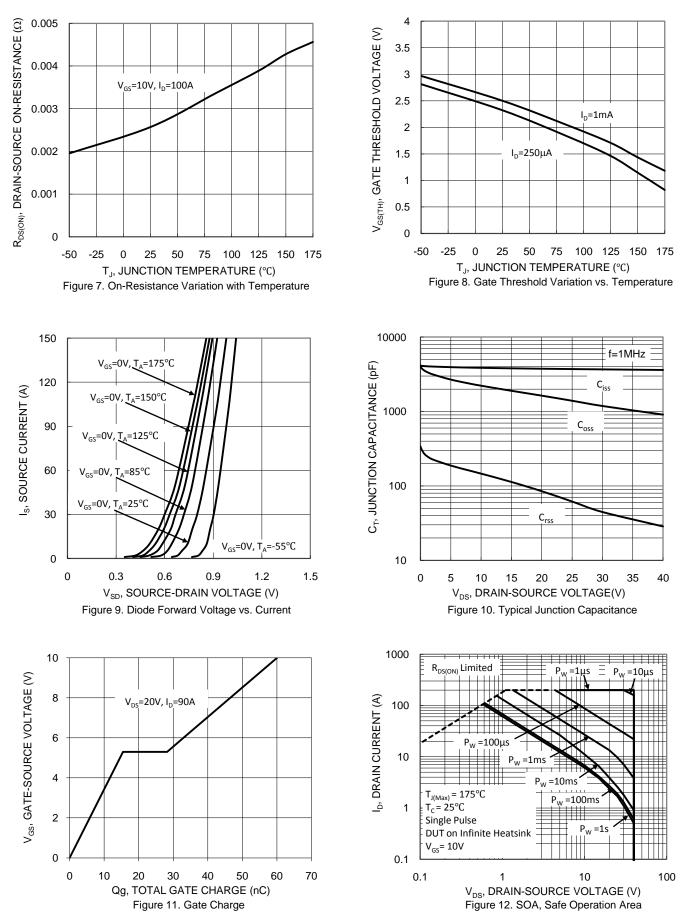
### DMTH4004SCTB



NEW PRODUCT

DMTH4004SCTB Document number: DS37328 Rev. 3 - 2

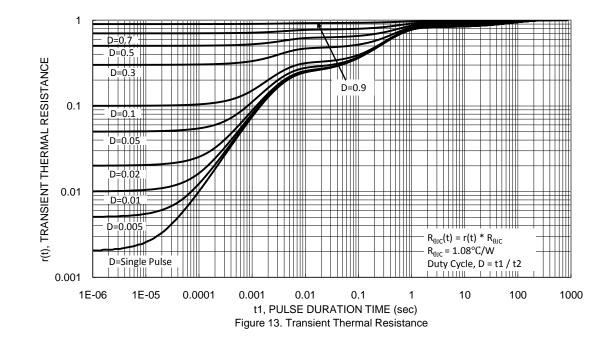




NEW PRODUCT

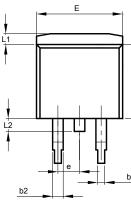
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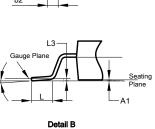


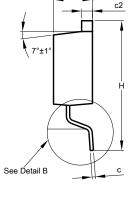


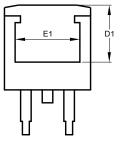
# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.









TO263AB (D2PAK)					
Dim	Min	Max	Тур		
Α	4.07	4.82	-		
A1	0.00	0.25	-		
b	0.51	0.99	-		
b2	1.15	1.77	-		
С	0.356	0.73	-		
c2	1.143	1.65	-		
D	8.39	9.65	-		
D1	6.55	6.95	-		
e	:	2.54 TYP			
Е	9.66	10.66	-		
E1	6.23	8.23	-		
Н	14.61	15.87	-		
L	1.78	2.79	-		
L1	-	1.67	-		
L2	-	1.77	-		
L3	-	-	0.254		
а	0°	8°	-		
All D	All Dimensions in mm				

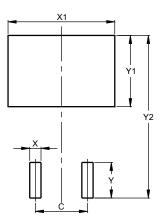
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# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	5.08
Х	1.10
X1	10.41
Y	3.50
Y1	7.01
Y2	15.99

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